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CENTRAL FAX CENTER****AUG 18 2006****In the Claims**

Claims 22-24, 26, and 28-31 are pending in the application with new claims 30 and 31 added herein.

Claims 1-21 (canceled).

22. (previously presented) A capacitor construction comprising:
an opening in an insulative layer over a substrate, the opening having sides and a bottom;
a hemispherical grain polysilicon layer over the sides of the opening but not over the bottom;
a conformal first capacitor electrode containing TiN on the polysilicon, the first electrode being sufficiently thin that the first electrode has a rugged outer surface with an outer surface area per unit area greater than an outer surface area per unit area of the substrate underlying the first electrode;
a capacitor dielectric layer on the first electrode; and
a second capacitor electrode over the dielectric layer.

23. (previously presented) The construction of claim 22 wherein the polysilicon is undoped.

24. (previously presented) The construction of claim 22 wherein the polysilicon comprises spaced apart grains.

25. (canceled).

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26. (previously presented) The construction of claim 22 wherein the dielectric layer comprises Ta_2O_5 , ZrO_2 , WO_3 , Al_2O_3 , HfO_2 , barium strontium titanate, or strontium titanate.

27. (canceled).

28. (previously presented) A capacitor construction comprising:
an opening in an insulative layer over a substrate, the opening having sides and a bottom;

a HSG polysilicon layer over the sides of the opening but not over the bottom;

a conformal first capacitor electrode containing TiN on the HSG polysilicon layer but not comprising the HSG polysilicon layer as part of the first electrode, the first electrode being sufficiently thin that the first electrode has a rugged outer surface with an outer surface area per unit area greater than a surface area per unit area of the sides of the opening over which the HSG polysilicon layer is formed;

a capacitor dielectric layer on the first electrode; and

a second capacitor electrode over the dielectric layer.

29. (previously presented) The construction of claim 28 wherein the first electrode also has an inner surface area per unit area that is greater than the surface area per unit area of the sides of the opening.

30. (new) The construction of claim 22 wherein the first capacitor electrode is on and in contact with the polysilicon.

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31. (new) The construction of claim 28 wherein the first capacitor electrode is on and in contact with the HSG polysilicon layer.